

BSR16

PNP General Purpose Amplifier

- This device designed for use as general purpose amplifier and switches requiring collector currents to 500mA.
- · Sourced from Process 63.
- See BCW68G for Characteristics.



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{CBO}	Collector-Base Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5.0	V
Ic	Collector Current - Continuous	-800	mA
T _J , T _{ST}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted Symbol **Parameter Test Condition** Min. Тур. Max. Units **Off Characteristics** Collector-Emitter Breakdown Voltage $BV_{(BR)CEO}$ $I_C = -10 \text{mA}, I_B = 0$ ٧ -60 Collector-Base Breakdown Voltage $I_C = -100\mu A, I_E = 0$ ٧ BV_{(BR)CBO} -60 Emitter-Base Breakdown Voltage ٧ $I_E=-10\mu A,\ I_C=0$ -5.0 $BV_{(BR)EBO}$ Collector Cut-off Current $V_{CB} = -50V$ -10 nΑ I_{CBO} $V_{CB} = -50V, T_A = 150^{\circ}C$ -10 μΑ Collector Cut-off Current $V_{CE} = -30V, V_{EB} = -0.5V$ -50 nΑ I_{CEX} $V_{CE} = -30V, V_{EB} = -3.0V$ Reverse Base Current -50 nΑ I_{BEX} On Characteristics h_{FF} DC Current Gain $I_C = -0.1 \text{mA}, V_{CE} = -10 \text{V}$ 75 $I_C = -1.0 \text{mA}, V_{CE} = -10 \text{V}$ 100 $I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$ 100 $I_C = -150 \text{mA}, V_{CE} = -10 \text{V}$ 100 300 $I_C = -500 \text{mA}, V_{CE} = -10 \text{V}$ 50 $I_C = -150 \text{mA}, I_B = -15 \text{mA}$ -0.4 ٧ V_{CE}(sat) Collector-Emitter Saturation Voltage $I_C = -500 \text{mA}, I_B = -50 \text{mA}$ -1.6 ٧ ٧ V_{BE}(sat) Base-Emitter Saturation Voltage $I_C = -150 \text{mA}, I_B = -15 \text{mA}$ -1.3 ٧ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$ -2.6 **Small Signal Characteristics** Current Gain Bandwidth Product $I_C = -50 \text{mA}, V_{CE} = -20 \text{V},$ $f = 100 \text{MHz}, T_A = 25 ^{\circ}\text{C}$ MHz 200 C_{cb} **Output Capacitance** $V_{CB} = -10V, I_E = 0, f = 1.0MHz$ 8.0 рF $V_{CB} = -2.0V$, $I_E = 0$, f = 1.0MHz**Emitter-Base Capacitance** 30 C_{eb} pF **Switching Characteristics** Turn-On Time $V_{CC} = -30V, I_{C} = -150mA,$ 45 t_{on} ns $I_{B1} = -15 \text{mA}$ **Delay Time** 10 ns 40 Rise Time ns t_r Turn-Off Time $V_{CC} = -30V, I_{C} = -150mA,$ 100 ns t_{off} $I_{B1} = I_{B2} = -15 \text{mA}$ t_{s} Storage Time 80 ns

Thermal Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

^{*} Device mounted on FR-4 PCB 40mm × 40mm × 1.5mm

Fall Time

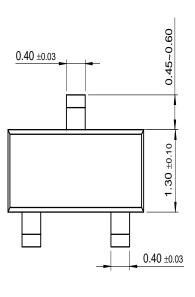
 t_f

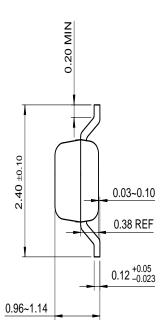
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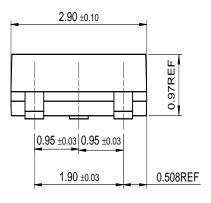
ns

Package Dimensions

SOT-23







Dimensions in Millimeters

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